



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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NPN General Purpose Transistor

BC847B / BC847C

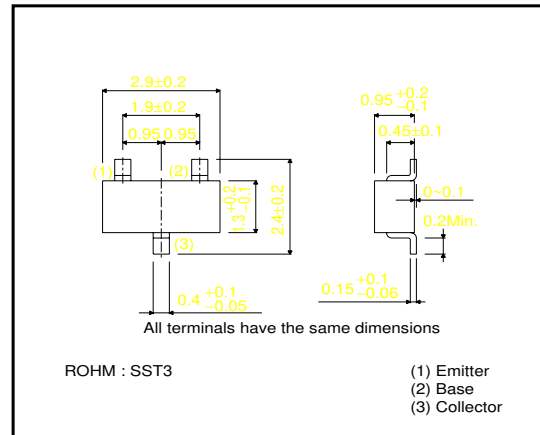
●Features

- 1) $BV_{CEO} < 45V$ ($I_C=1mA$)
- 2) Complements the BC857B.

●Package, marking, and Packaging specifications

Part No.	BC847B	BC847C
Packaging type	SST3	SST3
Marking	G1F	G1G
Code	T116	T116
Basic ordering unit (pieces)	3000	3000

●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	45	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	0.1	A
Collector power dissipation	P_C	0.2	W *
		0.35	
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55~+150	$^\circ C$

* When mounted on a 7×5×0.6mm ceramic board.

●Electrical characteristics ($T_a=25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	50	–	–	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	45	–	–	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	6	–	–	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	–	–	15	nA	$V_{CB}=30V$
		–	–	5	μA	$V_{CB}=30V, T_a=150^\circ C$
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	0.25	V	$I_C/I_B=10mA/0.5mA$
		–	–	0.6		$I_C/I_B=100mA/5mA$
Base-emitter saturation voltage	$V_{BE(on)}$	0.58	–	0.77	V	$V_{CE}/I_C=5V/10mA$
DC current transfer ratio	h_{FE}	200	–	450	–	$V_{CE}/I_C=5V/2mA$ BC847B
		420	–	800	–	$V_{CE}/I_C=5V/2mA$ BC847C
Transition frequency	f_T	–	200	–	MHz	$V_{CE}=5V, I_E=-20mA, f=100MHz$
Collector output capacitance	C_{ob}	–	3	–	pF	$V_{CB}=-10V, I_E=0, f=1MHz$
Emitter input capacitance	C_{ib}	–	8	–	pF	$V_{EB}=0.5V, I_C=0, f=1MHz$

●Electrical characteristic curves

The electrical characteristic curves for these products are the same as those of UMT222A, SST222A, MMST2222A and PN2222A.